

**AMENDMENTS TO THE SPECIFICATION**

Please amend the Specification pursuant to 37 C.F.R. § 1.121 as follows:

Please amend the text at page 3, line 16, bridging page 4, line 3, as follows:

According to another aspect of the present invention, there is also provided a method for growing a nitride semiconductor epitaxial layer, including a first step of growing a first nitride semiconductor epitaxial layer containing indium at a first temperature, a second step of growing a second nitride semiconductor epitaxial layer whose equilibrium vapor pressure of nitrogen is ~~higher~~ lower than that of the first nitride semiconductor epitaxial layer, on the first nitride semiconductor epitaxial layer at a second temperature, and a third step of releasing nitrogen from the first nitride semiconductor epitaxial layer by increasing a temperature to a third temperature higher than the second temperature to convert the first nitride semiconductor epitaxial layer into a metal layer.